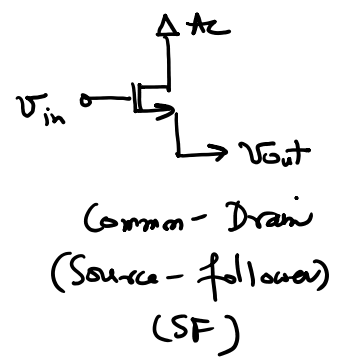
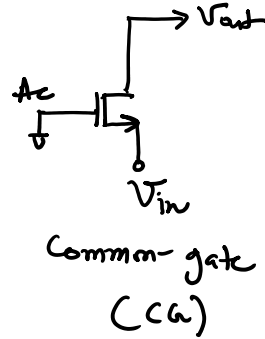
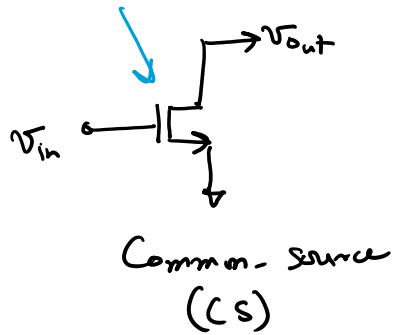
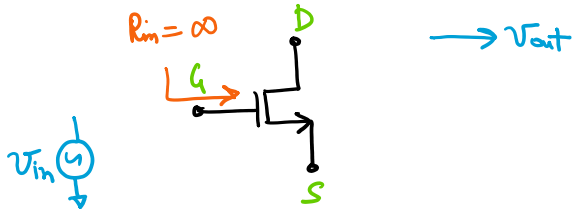


ECF 310 - Lecture 22

Wednesday, March 7, 2018 10:31 AM

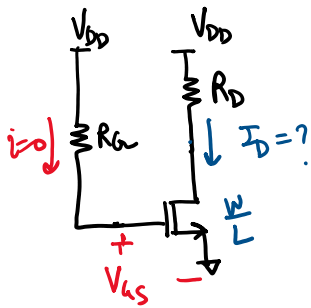
$$3C_2 = \frac{3.2}{1.2} = 3$$

* Small signal analysis



Common Source Amplifier (stage)

$V_{DD} = 1.8V$
180nm CMOS



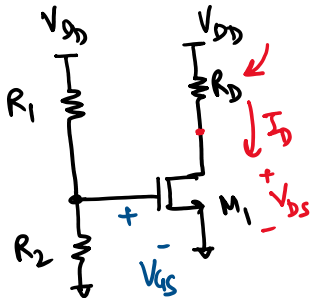
$$V_{GS} = V_{DD}$$

SAT: $I_D = \frac{1}{2} K_n \frac{W}{L} (V_{GS} - V_{THN})^2$

\downarrow
 V_{DD}

$\lambda \approx 0$

3-R biasing



$$V_{GS} = \frac{R_2}{R_1 + R_2} V_{DD}$$

for M_1 in SAT

$$I_D = \frac{1}{2} K_n \frac{W}{L} \left[V_{DD} \cdot \frac{R_2}{R_1 + R_2} - V_{THN} \right]^2$$

with proper choice of $\frac{W}{L}$, R_1 , R_2 we can set a desired I_D .

To keep M_1 in SAT:

$$V_{DS} \geq V_{GS} - V_{THN}$$

$$V_{DD} - I_D \cdot R_D \geq \frac{R_2}{R_1 + R_2} V_{DD} - V_{THN} \quad \leftarrow \text{Satisfy this to keep } M_1 \text{ in SAT}$$

$$I_D R_D \leq -\frac{R_2}{R_1 + R_2} V_{DD} + V_{DD} + V_{THN}$$

$$\Rightarrow I_D R_D \leq V_{DD} \left(\frac{R_1}{R_1 + R_2} \right) + V_{THN}$$

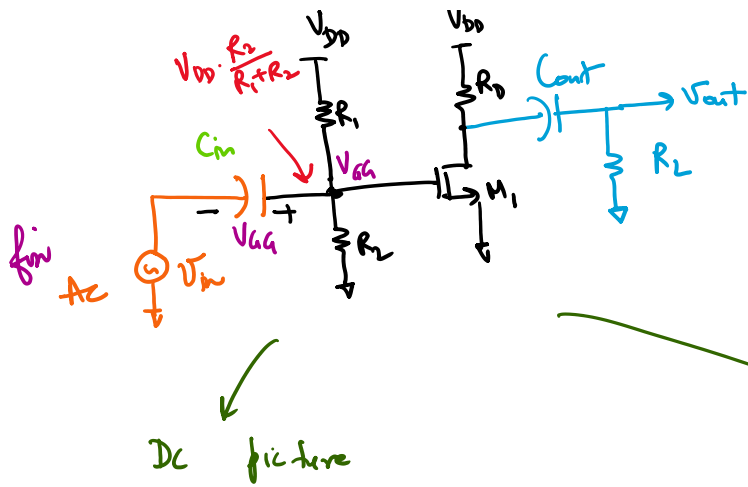
$I_D \uparrow$

$$V_{DD} \cdot \frac{R_1}{R_1 + R_2} \left[\frac{V_{DD}}{R_D} \right]$$

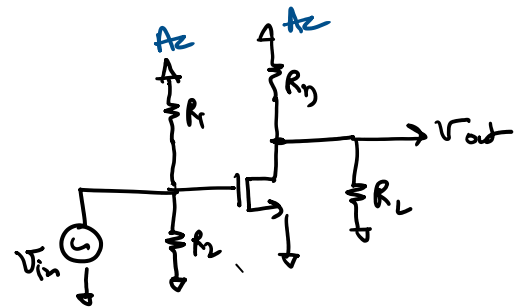
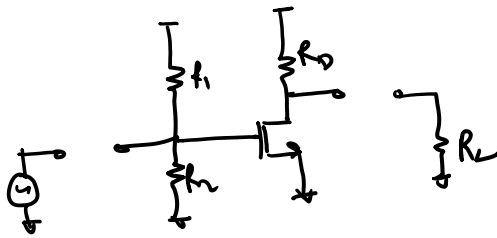
$$\frac{V_{DD}}{R_D} \xrightarrow{\text{Cont}} V_{out}$$

$$V_{GS} = \frac{R_2}{R_1 + R_2} V_{DD}$$

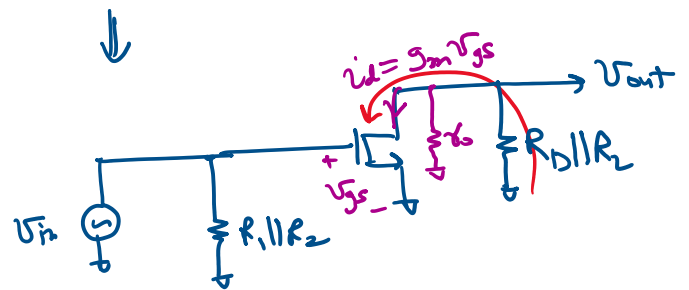
Coupling \Rightarrow DC Blocking



$C_{in} \rightarrow$ $\begin{cases} \text{DC Blocking} \\ \text{AC coupling} \\ \text{Capacitive Coupling} \end{cases}$



"lumping"



$$v_{out} = -g_m v_{gs} (r_o \parallel R_D \parallel R_L)$$

$$v_{out} = -g_m v_{in} (r_o \parallel R_D \parallel R_L)$$

$$a_v = \frac{v_{out}}{v_{in}} = -g_m (r_o \parallel R_D \parallel R_L)$$

$$r_o \gg R_D \parallel R_L$$

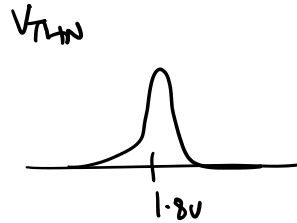
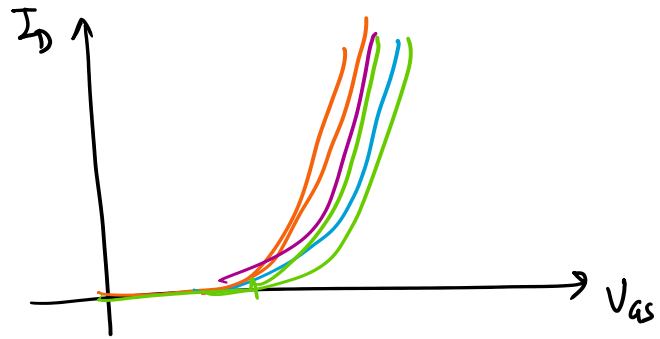
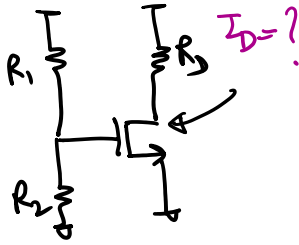
$$\rightarrow -g_m (R_D \parallel R_L)$$

See Book Examples

17.5, 6 & 7 for numerical Examples.

$$\tau = R_{eq} C > \frac{10}{f_{in}} \Leftrightarrow$$

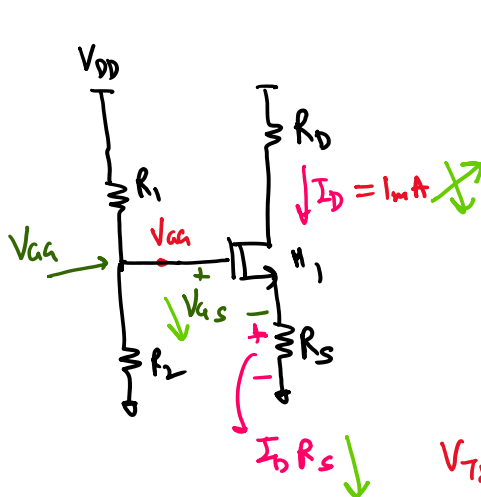
Bias RC time
constant > 10x
input
time-constant



Biasing is sensitive to MOSFET parameter variations
 $\rightarrow \underline{V_{THN}}$

× Need to desensitize I_D to variations in V_{THN} .

"4-R Biasing" \Rightarrow Source Degeneration



$V_{GS} = \frac{R_2}{R_1 + R_2} V_{DD} = V_{GS} + \underbrace{I_D R_S}_{\text{precise}}$
 large part of V_{GS} is dropped across R_S

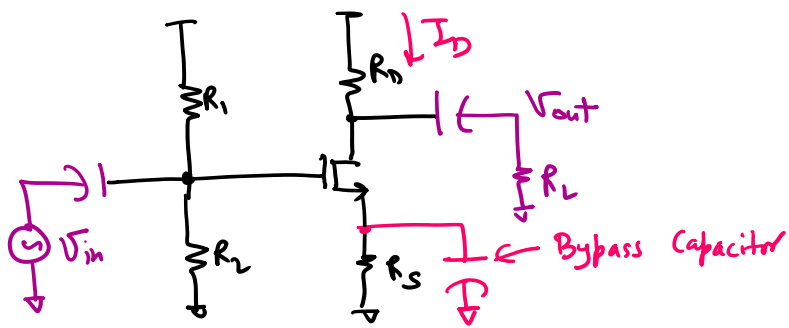
$I_D = \frac{1}{2} K_n \frac{W}{L} (V_{GS} - V_{THN})^2$
 $\downarrow \quad \downarrow$
 $0.35 \quad 0.3V$

$V_{THN} = 0.35V$
 $V_{THN} = 0.3V$

Negative feedback stabilizes I_D & V_{GS} & V_{DS} in this circuit

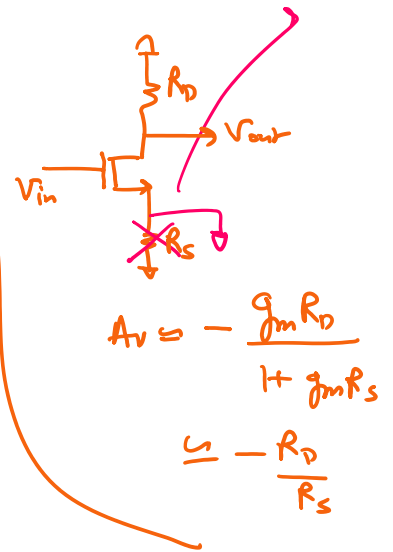
$$\Delta V_{THN} \Rightarrow \frac{\Delta I_D}{1 + g_m R_S}$$

-g_mR_D



$$V_{DS} = V_{DD} - I_D(R_D + R_S) \quad I_D = \frac{1}{2} \mu_n C_{ox} \frac{W}{L} (V_{GS} - V_{th})^2$$

$$V_{GS} = \frac{R_2}{R_1 + R_2} V_{DD} - I_D R_S$$



Do Bosh Ex. 17.9, 10

Simple Biasing

